MOSFET – Single, N-Channel, Small Signal, Gate ESD Protection, SC-75

30 V, 154 mA

Features

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players,
 Digital Cameras, PDA's, Video Games, Hand-Held Computers, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Paramo	Symbol	Value	Unit	
Drain-to-Source Voltage	V _{DSS}	30	V	
Gate-to-Source Voltage		V _{GS}	±10	V
Continuous Drain Current (Note 1)	Steady State = 25°C	I _D	154	mA
Power Dissipation (Note 1)	Steady State = 25°C	P _D	300	mW
Pulsed Drain Current $t_P \le 10 \mu s$		I _{DM}	618	mA
Operating Junction and St	T _J , T _{STG}	-55 to 150	°C	
Continuous Source Curre	I _{SD}	154	mA	
Lead Temperature for Solo (1/8" from case for 10 s)	TL	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	416	°C/W

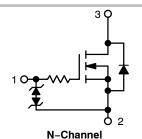
 Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).



ON Semiconductor®

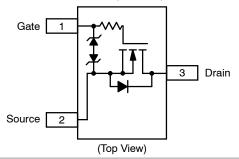
http://onsemi.com

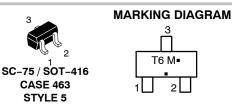
V _{(BR)DSS}	R _{DS(on)} Typ @ V _{GS}	I _D MAX (Note 1)	
20.14	1.4 Ω @ 4.5 V	454 4	
30 V	2.3 Ω @ 2.5 V	154 mA	



PIN CONNECTIONS

SC-75 (3-Leads)





T6 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

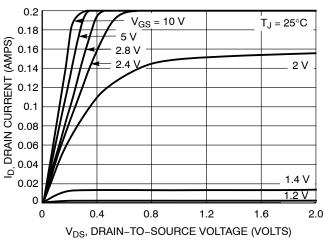
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•					
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 100 \mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 30 V			1.0	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V},$ $T = 85 ^{\circ}\text{C}$			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±10 V			±25	μА
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			±1.0	μА
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V, } V_{GS} = \pm 5 \text{ V}$ $T = 85 ^{\circ}\text{C}$			±1.0	μΑ
ON CHARACTERISTICS (Note 2)	•	•	•			
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS} = V_{GS}, I_{D} = 100 \mu A$	0.5	1.0	1.5	V
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 154 \text{ mA}$		1.4	7.0	
		V _{GS} = 2.5 V, I _D = 154 mA		2.3	7.5	Ω
Forward Transconductance	9FS	V _{DS} = 3 V, I _D = 154 mA		80		mS
CAPACITANCES						
Input Capacitance	C _{ISS}			11.5	20	
Output Capacitance	C _{OSS}	$V_{DS} = 5.0 \text{ V}, f = 1 \text{ MHz}, $ $V_{GS} = 0 \text{ V}$		10	15	pF
Reverse Transfer Capacitance	C _{RSS}			3.5	6.0	1
SWITCHING CHARACTERISTICS (Note 3)						
Turn-On Delay Time	t _{d(ON)}			13		ns
Rise Time	t _r	V _{GS} = 4.5 V, V _{DS} = 5.0 V,		15		
Turn-Off Delay Time	t _{d(OFF)}	$I_D = 75 \text{ mA}, R_G = 10 \Omega$		98		ns
Fall Time	t _f			60		
DRAIN-SOURCE DIODE CHARACTERISTICS	<u>.</u>					
Forward Diode Voltage	V_{SD}	V _{GS} = 0 V, I _S = 154 mA		0.77	0.9	V
	•					

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES



D_S, DRAIN-TO-SOURCE VOLTAGE (VOLTS)
Figure 1. On-Region Characteristics

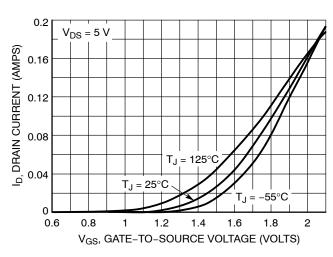


Figure 2. Transfer Characteristics

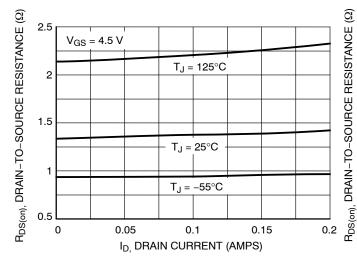


Figure 3. On–Resistance vs. Drain Current and Temperature

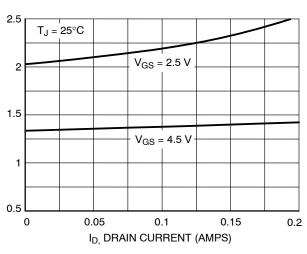


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

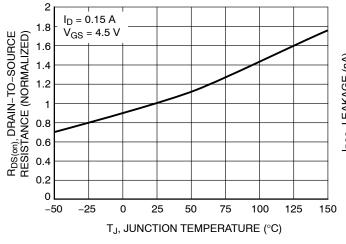


Figure 5. On–Resistance Variation with Temperature

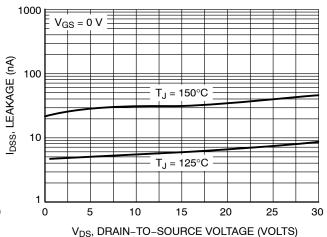
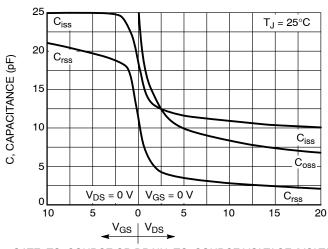
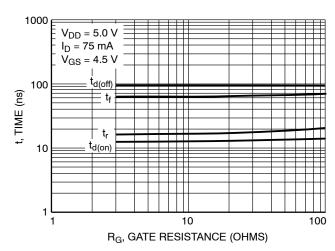


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES





GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

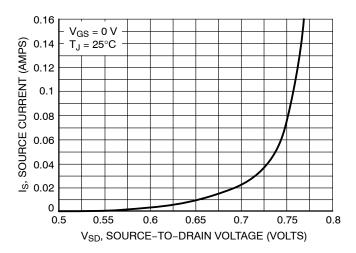


Figure 9. Diode Forward Voltage vs. Current

ORDERING INFORMATION

Device	Package	Shipping [†]
NTA7002NT1G	SC-75 (Pb-Free)	3000 / Tape & Reel
NVTA7002NT1G	SC-75 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

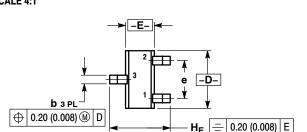
MECHANICAL CASE OUTLINE

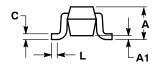




SC-75/SOT-416 CASE 463-01 **ISSUE G**

DATE 07 AUG 2015





STYLE 1: PIN 1. BASE 2. EMITTER

3. COLLECTOR

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.061	0.063	0.065
Е	0.70	0.80	0.90	0.027	0.031	0.035
е	1	.00 BSC)	0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.060	0.063	0.067

GENERIC MARKING DIAGRAM*



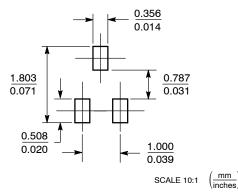
XX= Specific Device Code

Μ = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	

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